Oral presentation | 15. Crystal Engineering | 15.4 III-V-group nitride crystals

[18p-C5-1~19] 15.4 III-V-group nitride crystals
Thu. Sep 18, 2014 1:30 PM - 7:15 PM  C5 (Open Hall)
△: Young Scientist Oral Presentation Award Applied
▲: English Presentation
▼: Both Award Applied and English Presentation

1:30 PM - 2:00 PM

[18p-C5-1][JSAP Paper Award Speech] (30min.)
Performance and Reliability of Deep-Ultraviolet Light-Emitting Diodes Fabricated on AlN Substrates Prepared by Hydride Vapor Phase Epitaxy

○Toru Kinoshita¹,², Toshiyuki Obata¹, Toru Nagashima¹, Hiroyuki Yanagi¹, Baxter Moody³, Seiji Mita³, Shin-ichiro Inoue²,⁴, Yoshinao Kumagai⁵, Akinori Koukitu⁵, Zlatko Sitar³,⁶ (Tokuyama¹, Kobe University², HexaTech³, NICT⁴, Tokyo University of Agriculture and Technology⁵, North Carolina State University⁶)